

**SANYO**

No.3363

**2SB1467/2SD2218**

PNP/NPN Epitaxial Planar Silicon Transistors

General High-current  
Switching Applications**Applications**

- Relay drivers, high-speed inverters, converters

**Features**

- Micaless package facilitating mounting
- Low collector-to-emitter saturation voltage:  $V_{CE(sat)} = -0.5V(\text{PNP}), 0.4V(\text{NPN})$  max
- Large current capacity

( ) : 2SB1467

**Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$** 

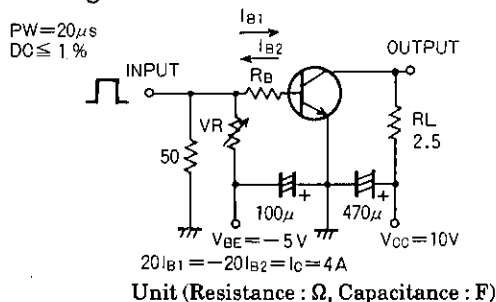
			unit
Collector-to-Base Voltage	$V_{CB0}$	(-)60	V
Collector-to-Emitter Voltage	$V_{CE0}$	(-)30	V
Emitter-to-Base Voltage	$V_{EB0}$	(-)6	V
Collector Current	$I_C$	(-)8	A
Collector Current (Pulse)	$I_{CP}$	(-)15	A
Collector Dissipation	$P_C$	2	W
		20	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

 $T_c = 25^\circ\text{C}$ **Electrical Characteristics at  $T_a = 25^\circ\text{C}$** 

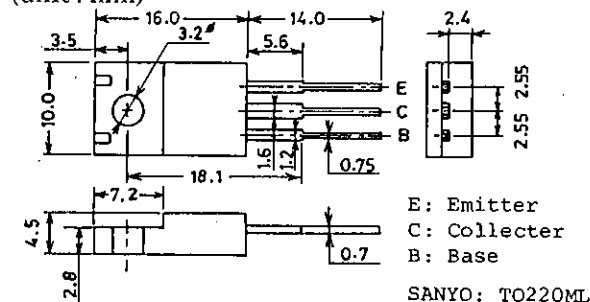
			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = (-)40V, I_E = 0$			(-)0.1	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	mA
DC Current Gain	$h_{FE(1)}^*$	$V_{CE} = (-)2V, I_C = (-)1A$	70*		280*	
	$h_{FE(2)}$	$V_{CE} = (-)2V, I_C = (-)4A$	30			
Gain-Bandwidth Product	$f_T$	$V_{CE} = (-)5V, I_C = (-)1A$		120		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)3A, I_B = (-)0.15A$			(-0.5)	V
					0.4	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)1mA, I_E = 0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)30			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)1mA, I_C = 0$	(-)6			V
Turn-ON time	$t_{on}$	See specified Test Circuit.		0.1		$\mu\text{s}$
Storage Time	$t_{stg}$	Same as above.		(0.2)0.5		$\mu\text{s}$
Fall Time	$t_f$	Same as above.		0.03		$\mu\text{s}$

\* : The 2SB1467/2SD2218 are classified by 1A  $h_{FE}$  as follows :

70 Q 140	100 R 200	140 S 280
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**Switching Time Test Circuit****Package Dimensions 2041**

(unit : mm)

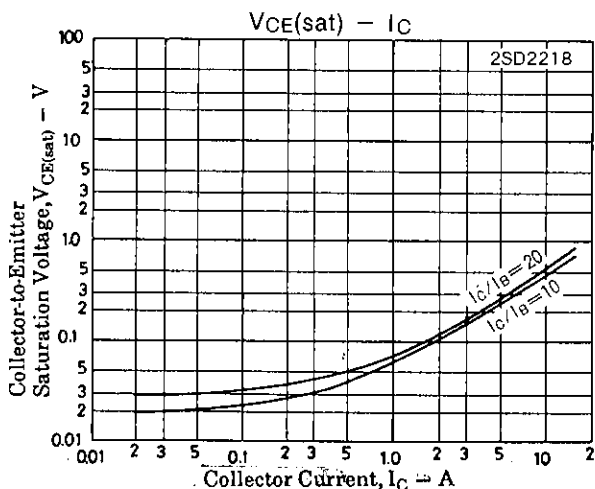
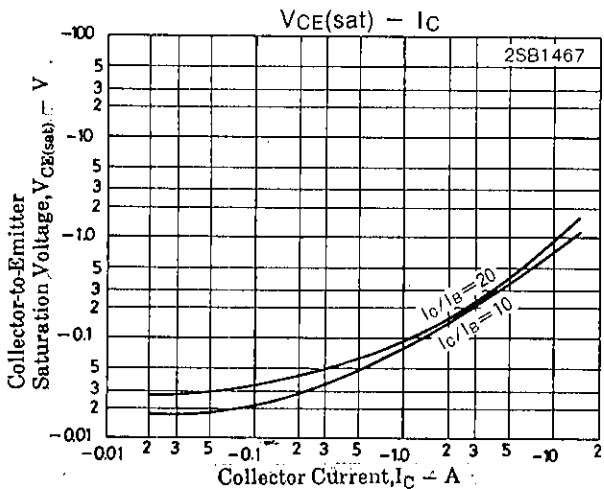
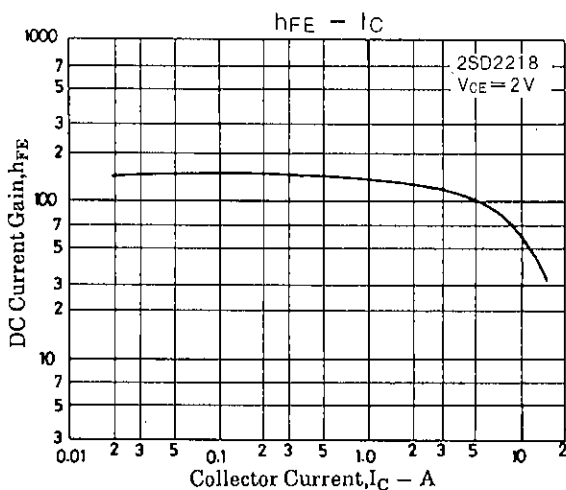
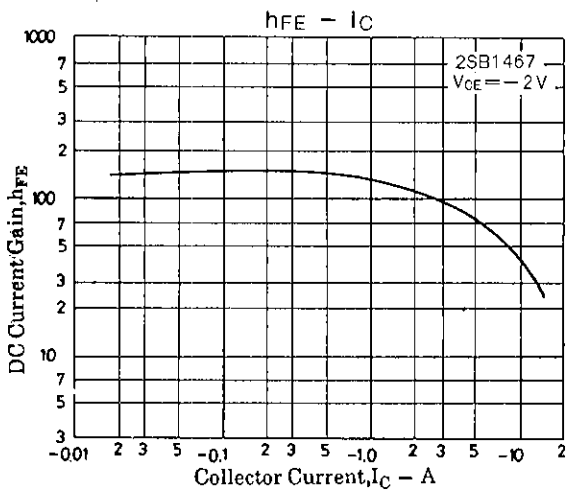
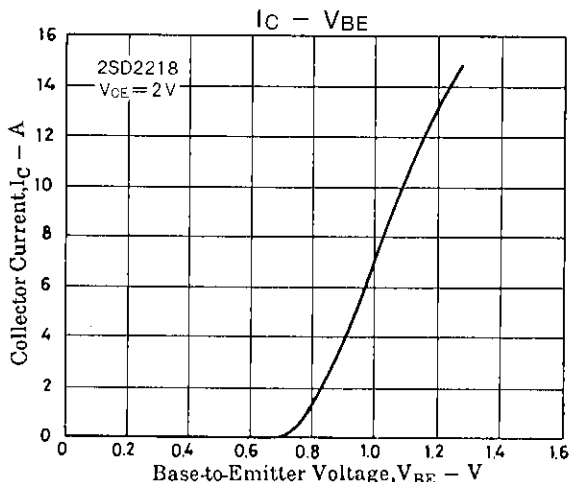
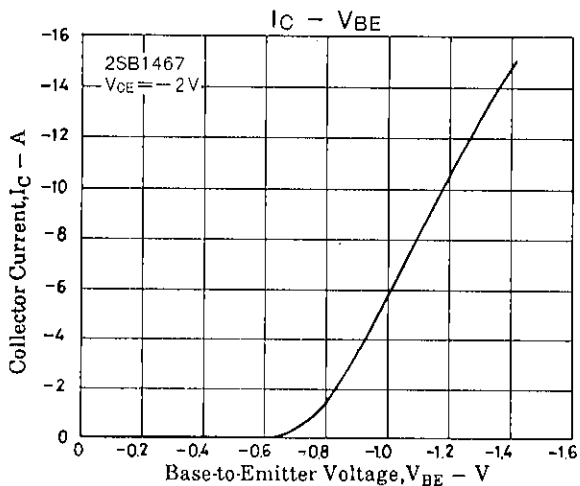
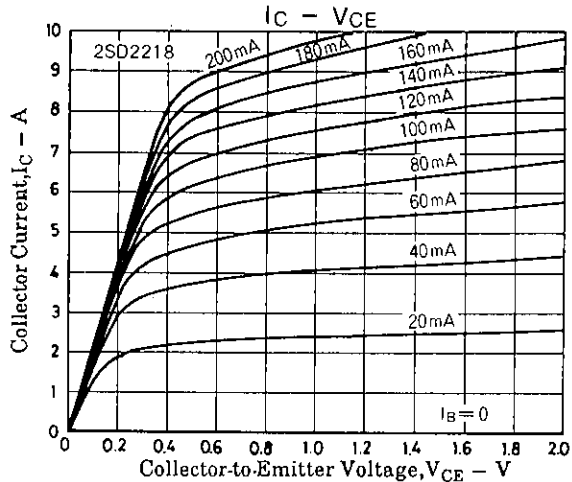
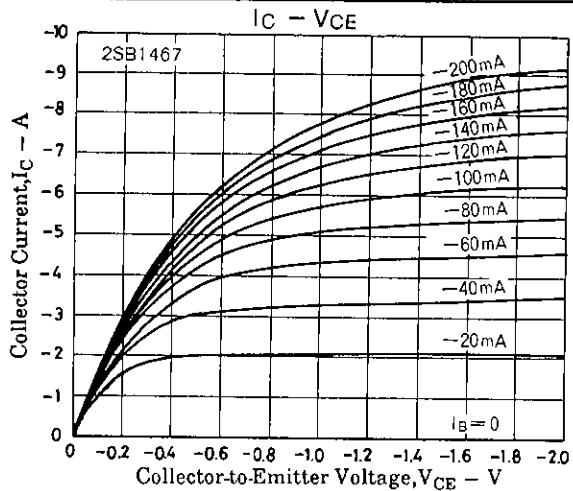
E: Emitter  
C: Collector  
B: Base

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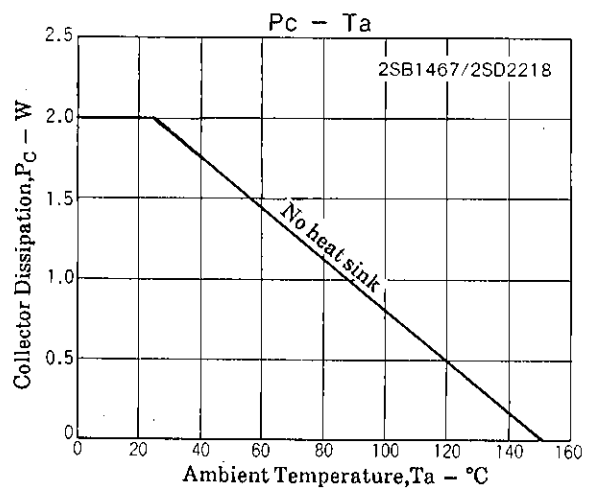
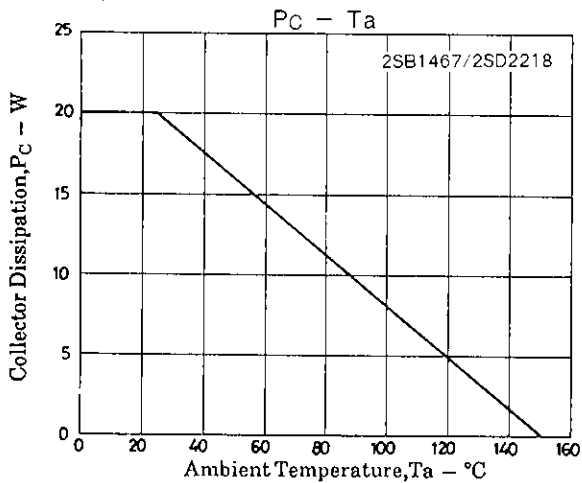
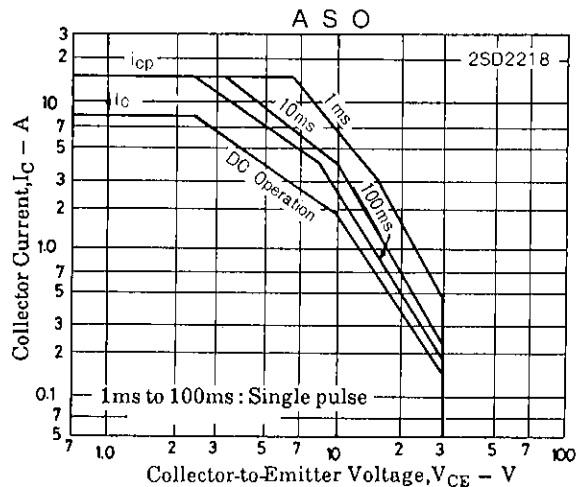
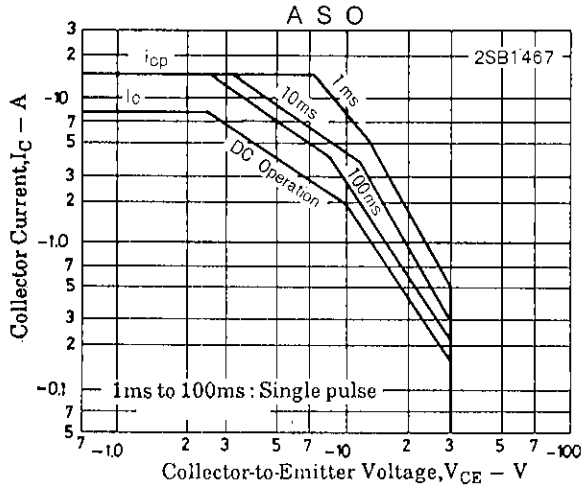
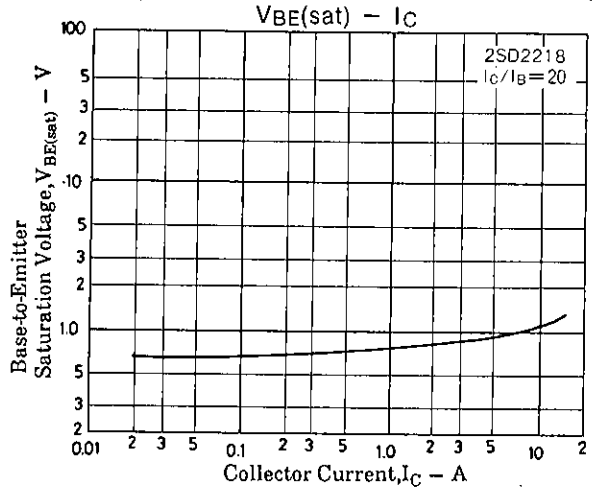
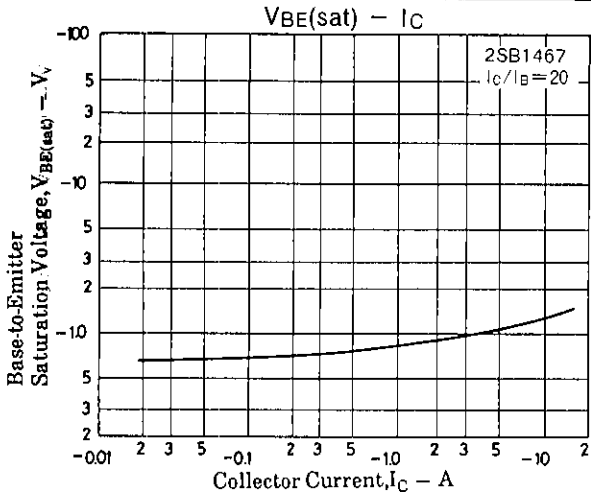
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